



DESERT SILICON, INC.

NOVEL SOLUTIONS FOR CLEAN TECHNOLOGY

WAFER BONDING

Wafer Size Up to 150mm	Process Temperature 350°C	Bonding Agent Cyclotene 3022™
Chamber Configuration Single	Temperature ramp Controlled at 6°/min up/down	Temperature Control Resistance and IR heating and water cooling

Benefits

- Almost any flat substrates can be bonded to each other, including silicon, GaAs, InP, glass, quartz, ceramic, aluminum and other metals.
- Wafers with thin films, such as oxides, metals, nitrides and others, can also be bonded

Typical Application

Adhesive bonding for typical substrate-to-substrate designs

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